# Vol. 8: June 2003

**Color Code:**
Red – Plasma Etching
Blue – Advanced Devices

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http://patft.uspto.gov/netahtml/srchnum.htm

| US Patent Nr. | Title | Assignee | Filed | Date of Patent |
|---|---|---|---|---|
| 6,562,187 | Methods and apparatus for determining an etch endpoint in a plasma processing system | Lam Research Corporation | 2/23/01 | 5/13/03 |
| 6,562,665 | Fabrication of a field effect transistor with a recess in a semiconductor pillar in SOI technology | Advanced Micro Devices, Inc. | 10/16/00 | 5/13/03 |
| 6,563,131 | Method and structure of a dual/wrap-around gate field effect transistor | International Business Machines Corporation | 6/2/00 | 5/13/03 |
| 6,563,152 | Technique to obtain high mobility channels in MOS transistors by forming a strain layer on an underside of a channel | Intel Corporation | 12/29/00 | 5/13/03 |
| 6,563,183 | Gate array with multiple dielectric properties and method for forming same | Advanced Micro Devices, Inc. | 2/28/02 | 5/13/03 |
| 6,564,114 | Determining endpoint in etching processes using real-time principal components analysis of optical emission spectra | Advanced Micro Devices, Inc. | 1/26/00 | 5/13/03 |

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| 6,566,177 | Silicon-on-insulator vertical array device trench capacitor DRAM | International Business Machines Corporation | 10/25/99 | 5/20/03 |
| 6,566,213 | Method of fabricating multi-thickness silicide device formed by disposable spacers | Advanced Micro Devices, Inc. | 4/2/01 | 5/20/03 |
| 6,566,215 | Method of fabricating short channel MOS transistors with source/drain extensions | Chartered Semiconductor Manufacturing Ltd. | 6/6/02 | 5/20/03 |
| 6,566,236 | Gate structures with increased etch margin for self-aligned contact and the method of forming the same | Integrated Device Technology, Inc. | 4/26/00 | 5/20/03 |
| 6,566,270 | Integration of silicon etch and chamber cleaning processes | Applied Materials Inc. | 9/15/00 | 5/20/03 |
| 6,566,704 | Vertical nano-size transistor using carbon nanotubes and manufacturing method thereof | Samsung Electronics Co. | 6/27/01 | 5/20/03 |
| 6,567,717 | Feed-forward control of TCI doping for improving mass-production-wise, statistical distribution of critical performance parameters in semiconductor devices | Advanced Micro Devices, Inc. | 1/19/00 | 5/20/03 |
| 6,569,736 | Method for fabricating square polysilicon spacers for a split gate flash memory device by multi-step polysilicon etch | Taiwan Semiconductor Manufacturing Co. | 2/14/02 | 5/27/03 |
| 6,569,773 | Method for anisotropic plasma-chemical dry etching of silicon nitride layers using a gas mixture containing fluorine | TEMIC Semiconductor GmbH | 12/19/99 | 5/27/03 |
| 6,569,774 | Method to eliminate striations and surface roughness caused by dry etch | Micron Technology, Inc. | 8/31/00 | 5/27/03 |

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| 6,569,775 | Method for enhancing plasma processing performance | Applied Materials, Inc. | 2/17/00 | 5/27/03 |
| 6,569,777 | Plasma etching method to form dual damascene with improved via profile | Taiwan Semiconductor Manufacturing Co. | 10/2/02 | 5/27/03 |
| 6,570,220 | Fabrication of deep submicron structures and quantum wire transistors using hard-mask transistor width definition | Intel Corporation | 3/14/00 | 5/27/03 |